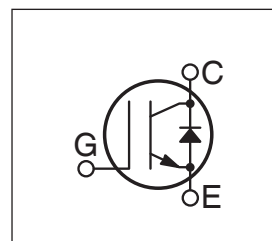
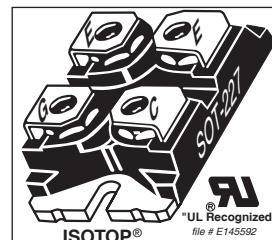


FAST IGBT & FRED

The Fast IGBT is a new generation of high voltage power IGBTs. Using Non-Punch through technology, the Fast IGBT combined with an Microsemi free wheeling Ultra Fast Recovery Epitaxial Diode (FRED) offers superior ruggedness and fast switching speed.

- Low Forward Voltage Drop
- High Freq. Switching to 20KHz
- RBSOA and SCSOA Rated
- Ultra Low Leakage Current
- Ultrafast Soft Recovery Anti-parallel Diode
- Intergrated Gate Resistor: Low EMI, High Reliability



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT40GF120JRDQ2	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	80	Amps
I_{C2}	Continuous Collector Current @ $T_C = 100^\circ\text{C}$	42	
I_{CM}	Pulsed Collector Current ^①	150	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	150A @ 1200V	
P_D	Total Power Dissipation	347	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 500\mu A$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 700\mu A, T_J = 25^\circ\text{C}$)	4.5	5.5	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 50A, T_J = 25^\circ\text{C}$)		2.5	3.0	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 50A, T_J = 125^\circ\text{C}$)		3.1		
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 25^\circ\text{C}$) ^②			200	μA
	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 125^\circ\text{C}$) ^②			1500	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 100	nA
$R_{G(int)}$	Intergrated Gate Resistor		5		Ω



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT40GF120JRDQ2

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		3460		pF
C_{oes}	Output Capacitance			385		
C_{res}	Reverse Transfer Capacitance			225		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 50A$		9.5		V
Q_g	Total Gate Charge ^③			340		nC
Q_{ge}	Gate-Emitter Charge			30		
Q_{gc}	Gate-Collector ("Miller") Charge			205		
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 1.0\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 1200V$	150			A
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 1.0\Omega$ ^⑦ $T_J = +25^\circ C$		25		ns
t_r	Current Rise Time			43		
$t_{d(off)}$	Turn-off Delay Time			260		
t_f	Current Fall Time			70		
E_{on1}	Turn-on Switching Energy ^④			3600		μJ
E_{on2}	Turn-on Switching Energy (WithDiode) ^⑤			4675		
E_{off}	Turn-off Switching Energy ^⑥			2640		
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 1.0\Omega$ ^⑦ $T_J = +125^\circ C$		25		ns
t_r	Current Rise Time			43		
$t_{d(off)}$	Turn-off Delay Time			300		
t_f	Current Fall Time			95		
E_{on1}	Turn-on Switching Energy ^④			3750		μJ
E_{on2}	Turn-on Switching Energy (WithDiode) ^⑤			6400		
E_{off}	Turn-off Switching Energy ^⑥			3400		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			0.36	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			1.1	
$V_{Isolation}$	RMS Voltage (50-60Hz Sinusoidal Waveform from Terminals to Mounting Base for 1 Min.)	2500			Volts
W_T	Package Weight		1.03		oz
			29.2		gm
Torque	Maximum Terminal & Mounting Torque			10	lb•in
				1.1	N•m

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and diode leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦ R_G is external gate resistance, not including $R_{G(int)}$ nor gate driver impedance. (MIC4452)

Mircosemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT40GF120JRDQ2

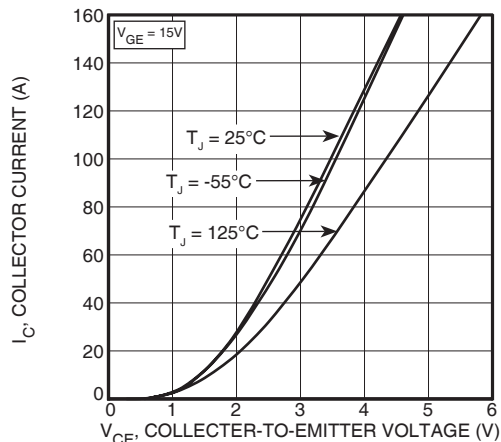


FIGURE 1, Output Characteristics($T_J = 25^{\circ}\text{C}$)

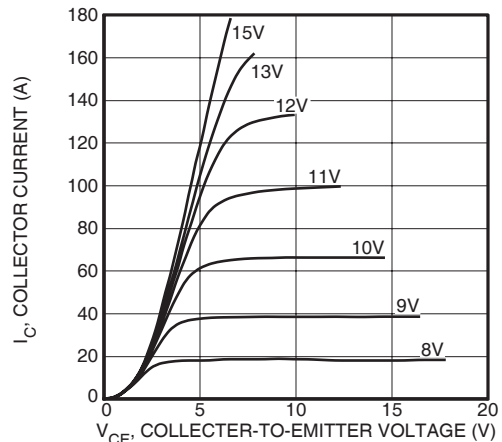


FIGURE 2, Output Characteristics ($T_J = 125^{\circ}\text{C}$)

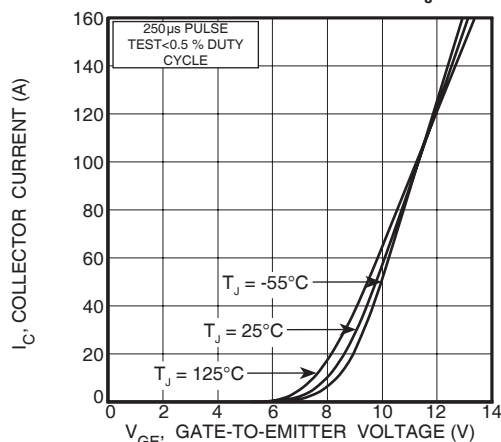


FIGURE 3, Transfer Characteristics

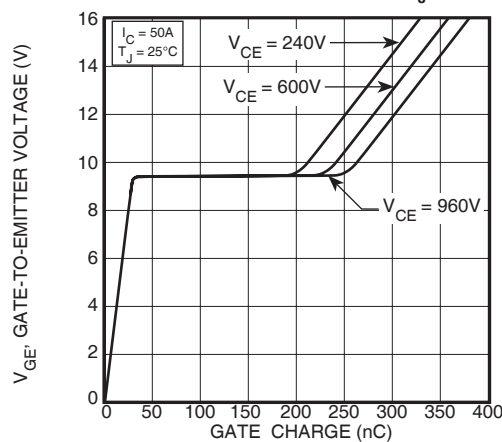


FIGURE 4, Gate Charge

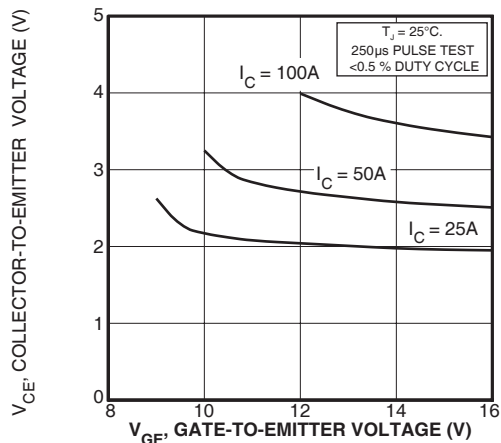


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

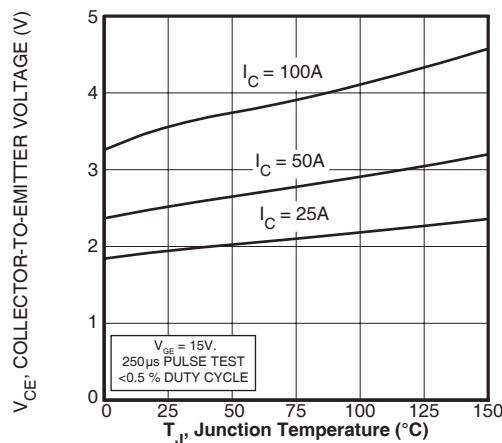


FIGURE 6, On State Voltage vs Junction Temperature

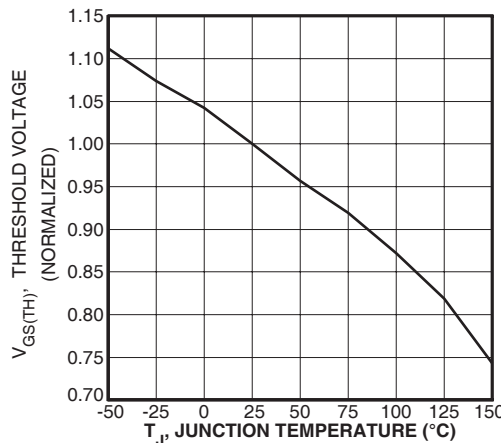


FIGURE 7, Threshold Voltage vs. Junction Temperature

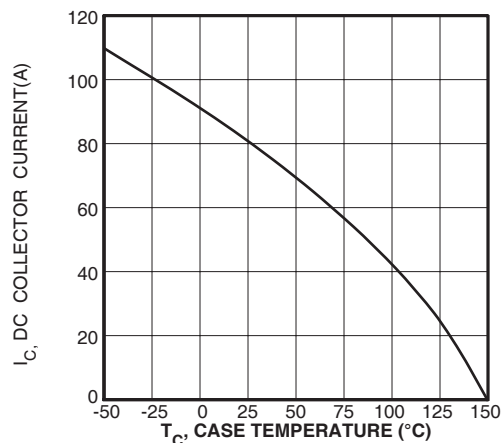


FIGURE 8, DC Collector Current vs Case Temperature

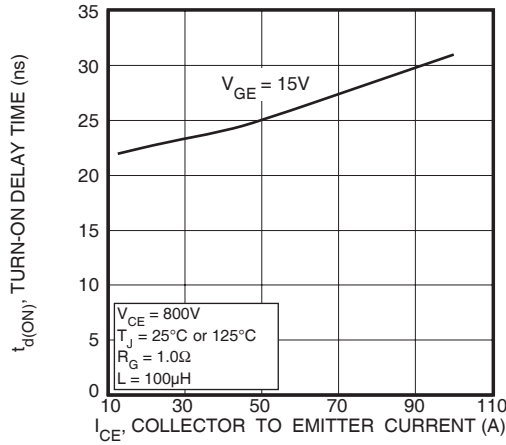


FIGURE 9, Turn-On Delay Time vs Collector Current

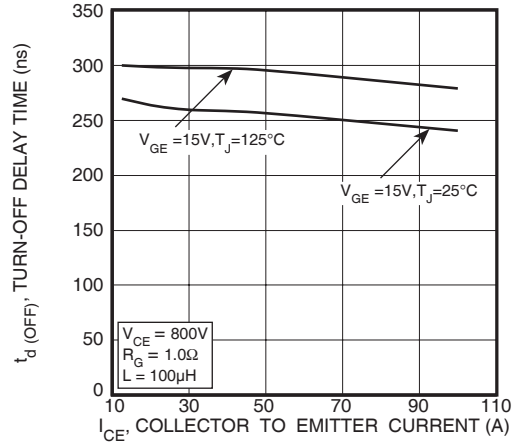


FIGURE 10, Turn-Off Delay Time vs Collector Current

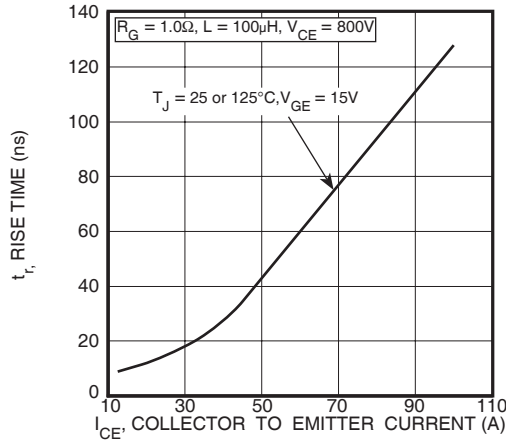


FIGURE 11, Current Rise Time vs Collector Current

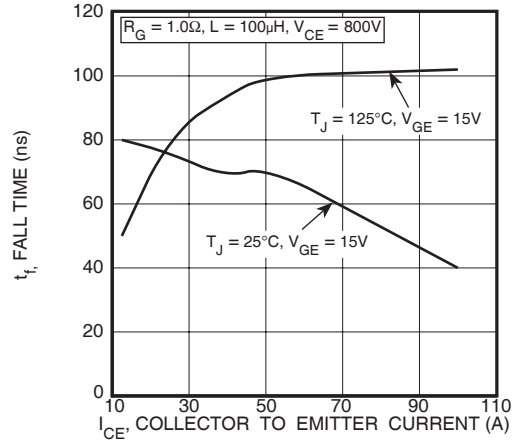


FIGURE 12, Current Fall Time vs Collector Current

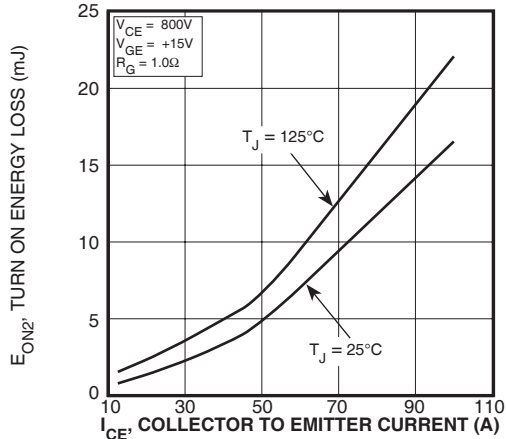


FIGURE 13, Turn-On Energy Loss vs Collector Current

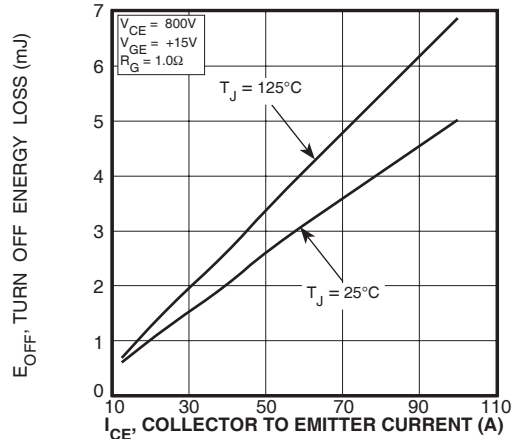


FIGURE 14, Turn Off Energy Loss vs Collector Current

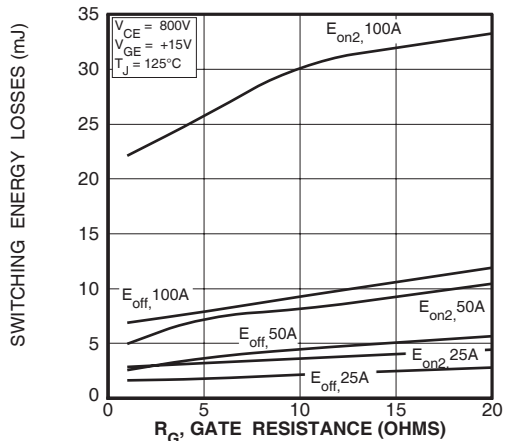


FIGURE 15, Switching Energy Losses vs. Gate Resistance

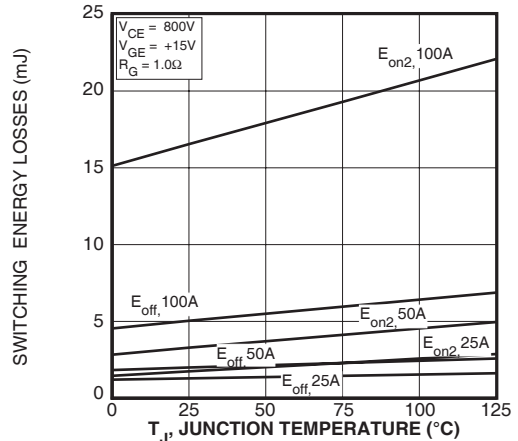


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

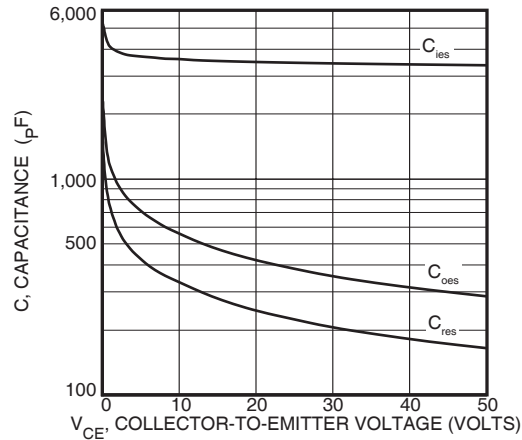


Figure 17, Capacitance vs Collector-To-Emitter Voltage

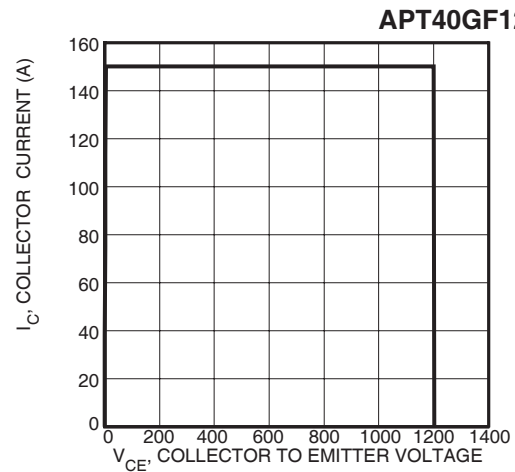


Figure 18, Minimum Switching Safe Operating Area

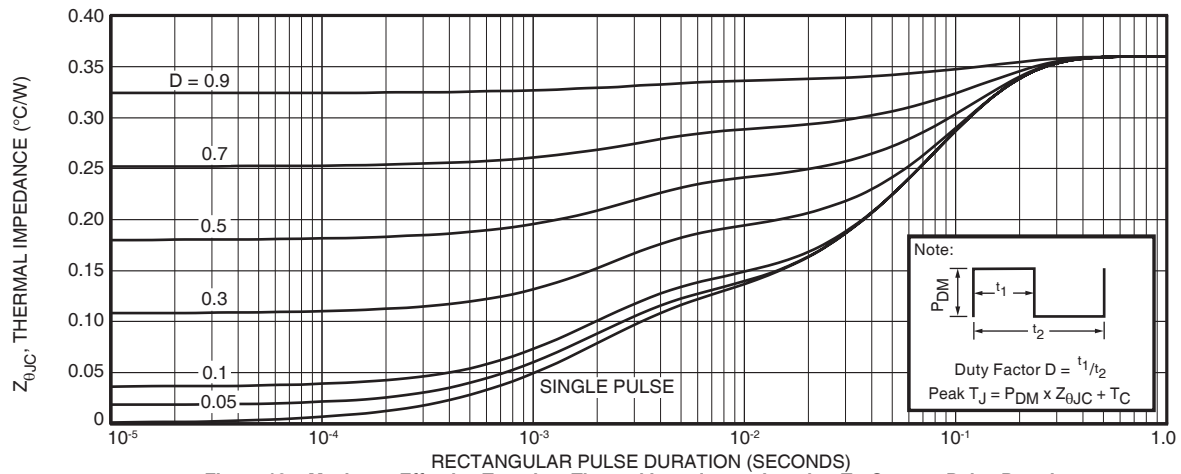


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

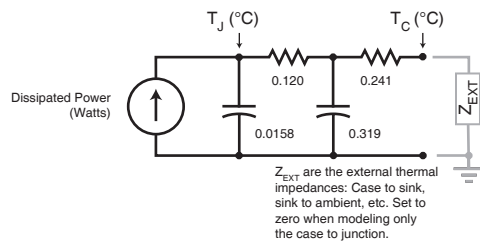


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

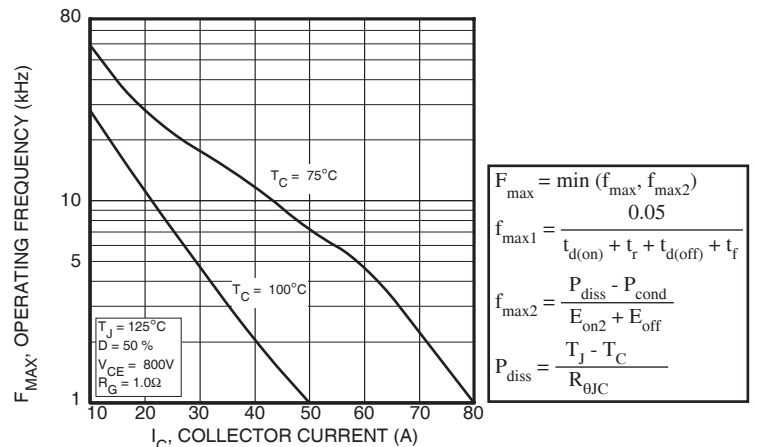


Figure 20, Operating Frequency vs Collector Current

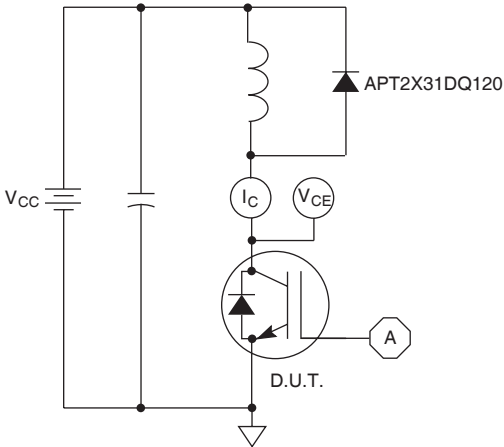


Figure 21, Inductive Switching Test Circuit

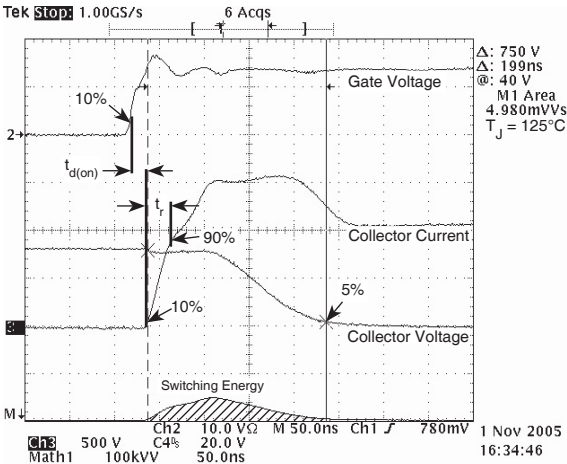


Figure 22, Turn-on Switching Waveforms and Definitions

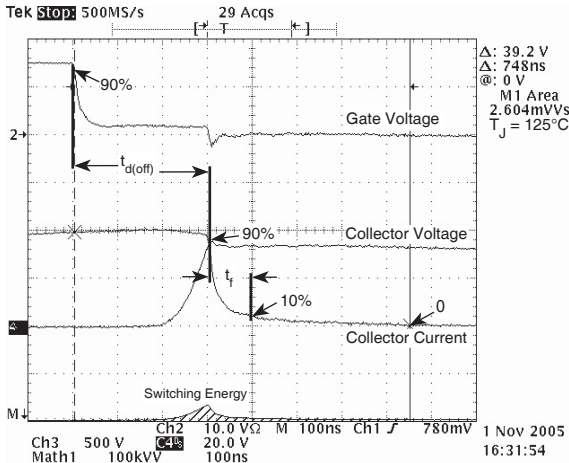


Figure 23, Turn-off Switching Waveforms and Definitions

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT40GF120JRDQ2			UNIT
$I_F(\text{AV})$	Maximum Average Forward Current ($T_C = 89^\circ\text{C}$, Duty Cycle = 0.5)		30		Amps
$I_F(\text{RMS})$	RMS Forward Current (Square wave, 50% duty)		39		
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)		210		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage		$I_F = 50\text{A}$	3.06	Volts
			$I_F = 100\text{A}$	3.82	
			$I_F = 50\text{A}, T_J = 125^\circ\text{C}$	2.25	

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	25		ns
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 25^\circ\text{C}$	-	300		
Q_{rr}	Reverse Recovery Charge		-	360		nC
I_{RRM}	Maximum Reverse Recovery Current		-	4	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	380		ns
Q_{rr}	Reverse Recovery Charge		-	1700		nC
I_{RRM}	Maximum Reverse Recovery Current		-	8	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	160		ns
Q_{rr}	Reverse Recovery Charge		-	2550		nC
I_{RRM}	Maximum Reverse Recovery Current		-	28		Amps

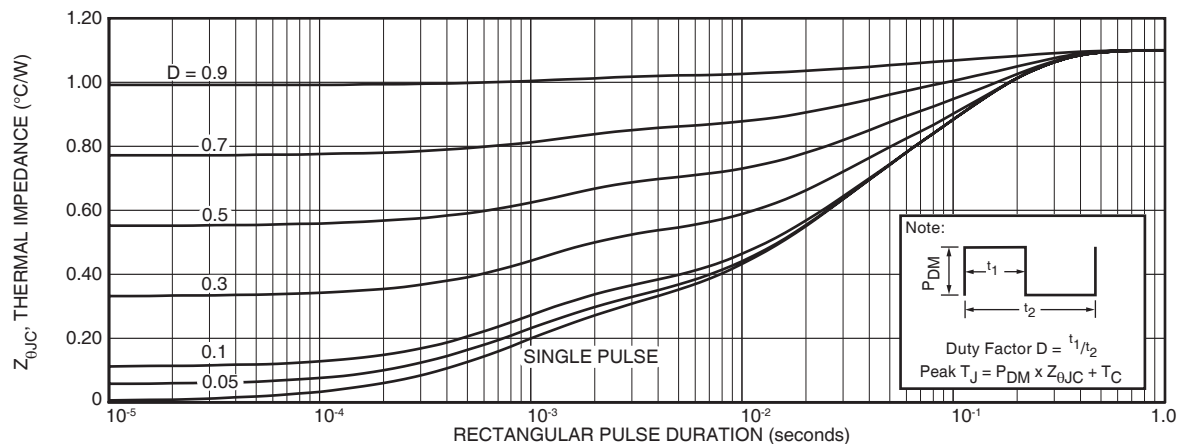


FIGURE 24a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

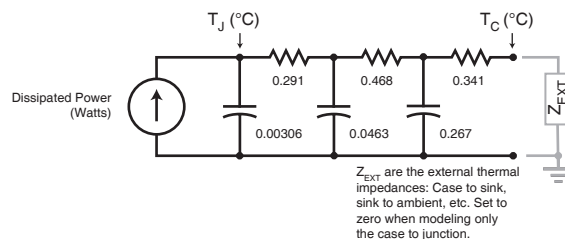


FIGURE 24b. TRANSIENT THERMAL IMPEDANCE MODEL

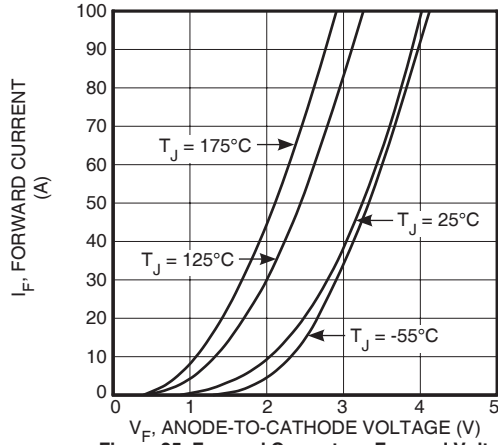


Figure 25. Forward Current vs. Forward Voltage

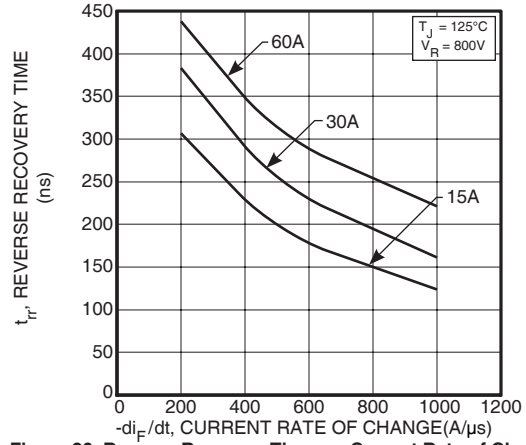


Figure 26. Reverse Recovery Time vs. Current Rate of Change

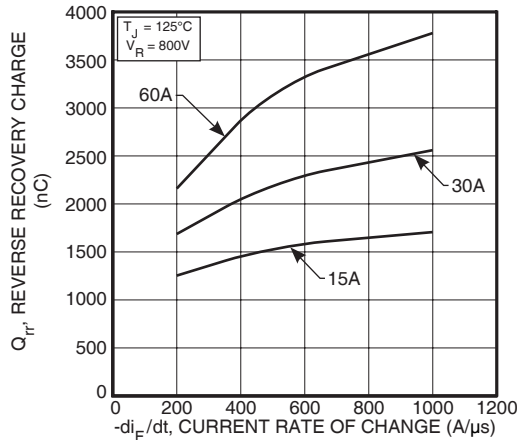


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

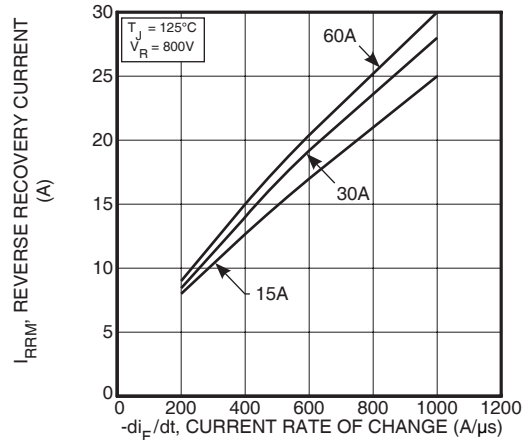


Figure 28. Reverse Recovery Current vs. Current Rate of Change

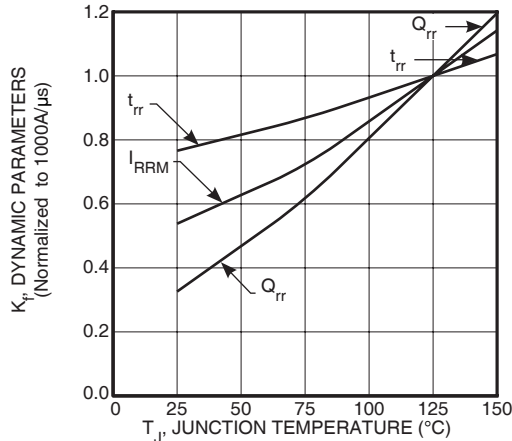


Figure 29. Dynamic Parameters vs. Junction Temperature

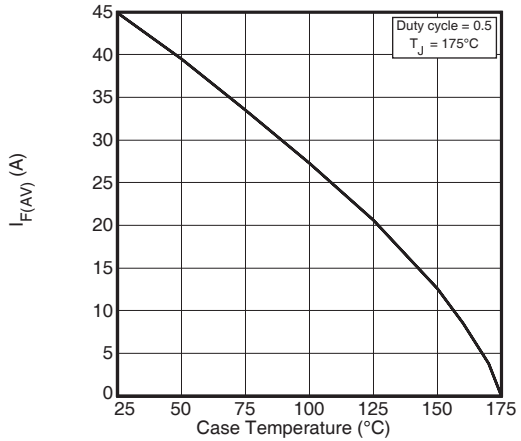


Figure 30. Maximum Average Forward Current vs. Case Temperature

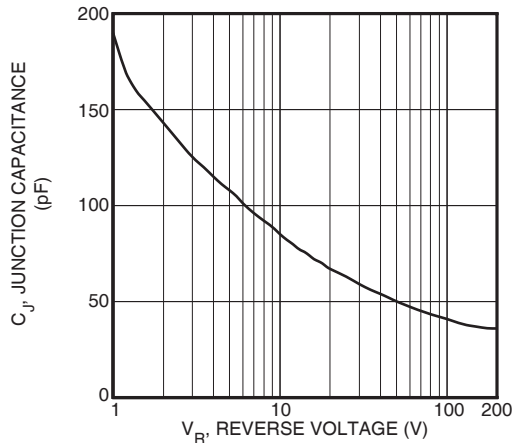


Figure 31. Junction Capacitance vs. Reverse Voltage

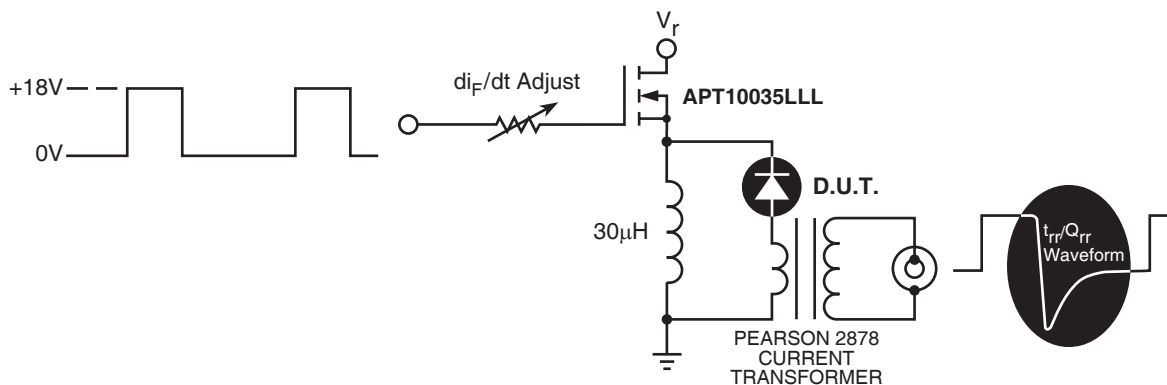


Figure 32. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

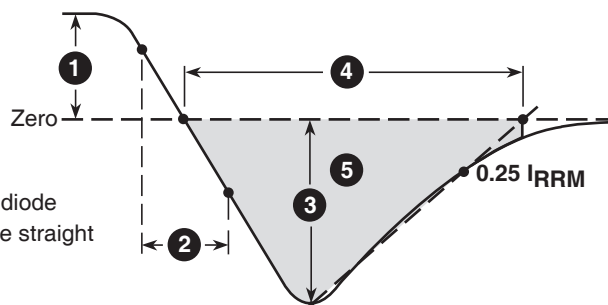
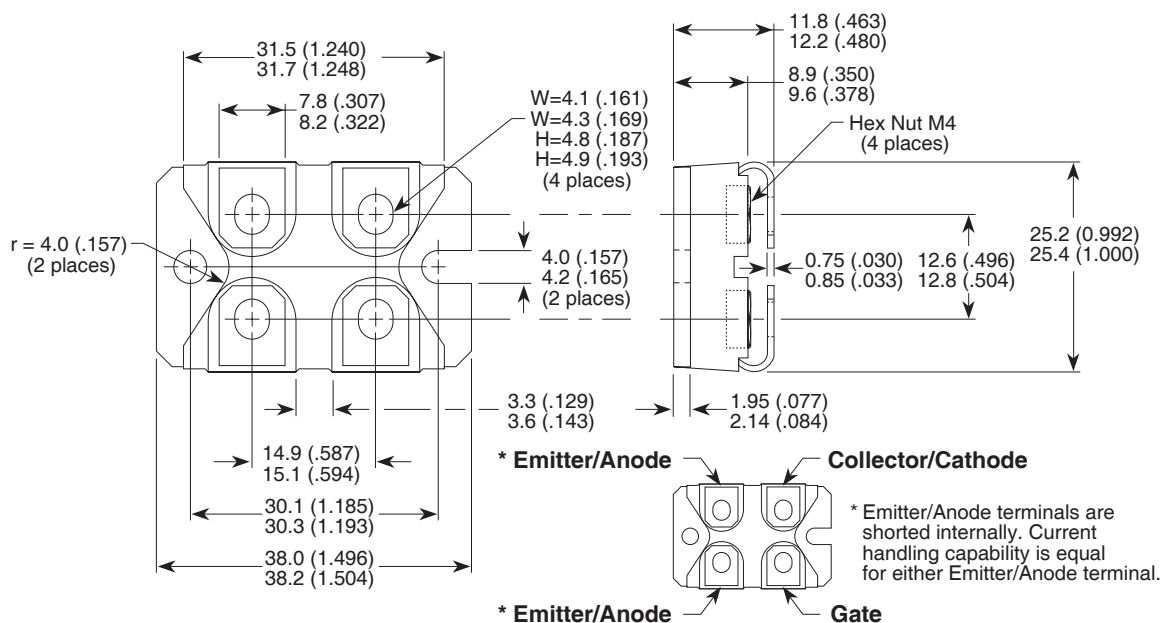


Figure 33. Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

ISOTOP® is a registered trademark of ST Microelectronics NV. Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.